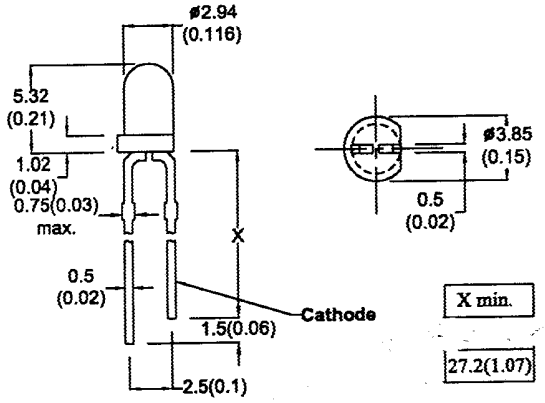
MICRO ELECTRONICS

MI32T-L

INFRARED EMITTING DIODE

DESCRIPTION

MI32T-L is GaAlAs infrared emiitting diode molded in 3mm diameter clear transparent lens.



- All dimension in mm(inch)
- No Scale
- Tol. : +/-0.3mm

ABSOLUTE MAXIMUM RATINGS

Forward Current (Continuous)	100mA
Pulse Forward Current	1A*
Reverse Voltage (Continuous)	6V
Power Dissipation	160mW
Operating Temperature Range	-25 to +85°C
Lead Soldering Temperature (1/16" from body)	260°C for 5 sec.

* Pulse Width = 10μs, Duty Ratio = 0.01.

ELECTRO-OPTICAL CHARACTERISTICS (Ta=25°C)

PARAMETER	SYMBOL	MIN	TYP	MAX	UNIT	CONDITIONS
Radiant Power Output	Po	4.0	8.0		mW	IF=50mA
Forward Voltage	VF		1.28	1.8	V	IF=50mA
Reverse Current	IR			100	μA	VR=5V
Half Intensity Beam Angle	θHI		80		degree	IF=50mA
Peak Wavelength	$\lambda\rho$		940		nm	IF=50mA
Spectrum Line Half Width	$\Delta\lambda$		45		nm	IF=50mA

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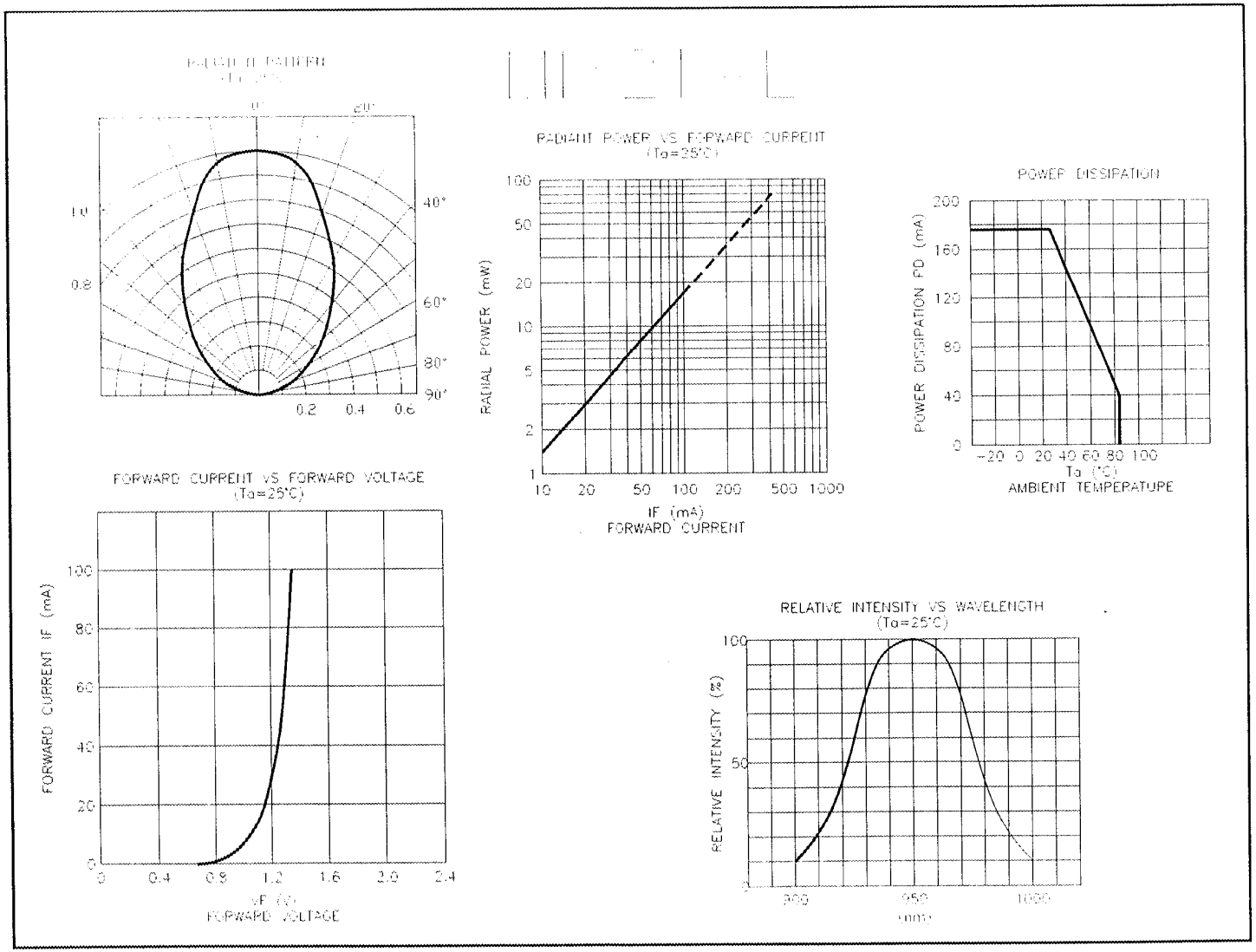
RADIANT POWER VS FORWARD CURRENT
(Ta=25°C)
RADIAL POWER (mW)
IF (mA)
FORWARD CURRENT
POWER DISSIPATION
POWER DISSIPATION PD (mA)
Ta (°C)
AMBIENT TEMPERATURE
FORWARD CURRENT VS FORWARD VOLTAGE
(Ta=25°C)
FORWARD CURRENT IF (mA)
VF (V)
FORWARD VOLTAGE
RELATIVE INTENSITY VS WAVELENGTH
(Ta=25°C)
RELATIVE INTENSITY (%)